

### 100V P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-100V	350mΩ @ V <sub>GS</sub> = -10V	-1.6A
-1007	450mΩ @ V <sub>GS</sub> = -6.0V	-1.4A

### **Description**

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

### **Features and Benefits**

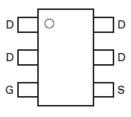
- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

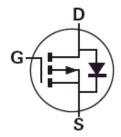
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
   Solderable per MIL-STD-202, Method 208
- Weight: 0.018 grams (Approximate)







Pin Out - Top View



**Equivalent Circuit** 

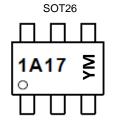
### Ordering Information (Notes 4 & 5)

Part Number	Qualification	Case	Packaging		
ZXMP10A17E6QTA	Automotive	SOT26	3,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



1A17 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M or  $\overline{M}$  = Month (ex: 9 = September)

### Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	С	D	Е	F	G	Н	ı	J	K	L	М	N

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

	Characteristic		Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-100	V
Gate-Source Voltage			V <sub>GS</sub>	±20	V
		(Note 7)		-1.6	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 7)}$	l <sub>D</sub>	-1.3	Α
		(Note 6)		-1.3	
Pulsed Drain Current	V <sub>GS</sub> = 10V	(Note 8)	I <sub>DM</sub>	-7.7	Α
Continuous Source Current (Body Diode)		(Note 7)	Is	-2.1	А
Pulsed Source Current (Body Diode) (Note 8)			I <sub>SM</sub>	-7.7	А

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)		1.1 8.8	W
Linear Derating Factor	(Note 7)	- P <sub>D</sub>	1.7 13.7	mW/°C
Thermal Resistance, Junction to Ambient	(Note 6)	D	113	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	73	C/VV
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

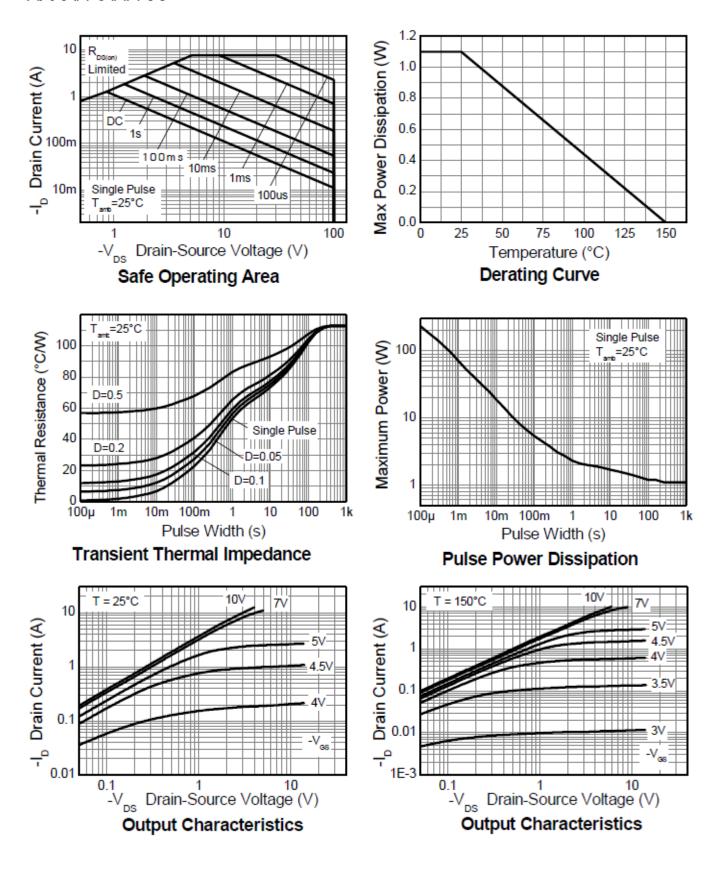
Characteristic	Symbol	Min	Тур	Max	Unit	Test Co	ondition	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-100	_	_	V	$I_D = -250 \mu A, V_{GS}$	= 0V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-0.5	μΑ	$V_{DS} = -100V, V_{GS}$	S = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS}$	= 0V	
ON CHARACTERISTICS						•		
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-2.0	_	-4.0	V	$I_D = -250 \mu A, V_{DS}$	= V <sub>GS</sub>	
Static Drain-Source On-Resistance (Note 9)				0.350	Ω	$V_{GS} = -10V, I_D = -10V$	-1.4A	
Static Drain-Source On-Resistance (Note 9)	R <sub>DS(ON)</sub>	_	_	0.450	12	$V_{GS} = -6V, I_D = -1$	.2A	
Forward Transconductance (Notes 9 & 10)	<b>G</b> fs	_	2.8	_	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -	-1.4A	
Diode Forward Voltage (Note 9)	$V_{SD}$	_	-0.85	-0.95	V	I <sub>S</sub> = -1.7A, V <sub>GS</sub> =	0V	
Reverse Recovery Time (Note 10)	t <sub>rr</sub>	_	33	_	ns	I <sub>S</sub> = -1.5A, di/dt = 100A/μs		
Reverse Recovery Charge (Note 10)	Q <sub>rr</sub>	_	48	_	nC			
DYNAMIC CHARACTERISTICS (Note 10)			•	•	•			
Input Capacitance	C <sub>iss</sub>	_	424	_	pF	501/1/	0) /	
Output Capacitance	Coss	_	36.6	_	pF	$V_{DS} = -50V, V_{GS}$ f = 1MHz	= UV	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	29.8	_	pF	71 = 1101112		
Total Gate Charge (Note 11)	Qg	_	7.1	_	nC	V <sub>GS</sub> = -6V		
Total Gate Charge (Note 11)	Qg	_	10.7	_	nC		$V_{DS} = -50V$	
Gate-Source Charge (Note 11)	Q <sub>gs</sub>	_	1.7	_	nC	V <sub>GS</sub> = -10V	$I_D = -1.4A$	
Gate-Drain Charge (Note 11)	$Q_{gd}$	_	3.8	_	nC			
Turn-On Delay Time (Note 11)	t <sub>D(on)</sub>	_	3	_	ns			
Turn-On Rise Time (Note 11)	t <sub>r</sub>	_	3.5	_	ns	$V_{DD} = -50V, V_{GS} = -10V$		
Turn-Off Delay Time (Note 11)	t <sub>D(off)</sub>		13.4	_	ns	$I_D = -1A, R_G \cong 6.0$	Ω	
Turn-Off Fall Time (Note 11)	t <sub>f</sub>	_	7.2	_	ns	1		

Notes:

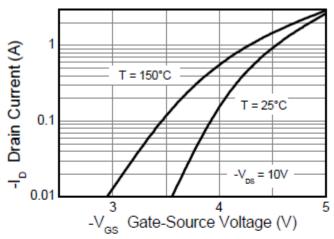
- 6. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Same as Note 6, except the device is measured at t ≤ 5 sec.

  8. Same as Note 6, except the device is pulsed with D = 0.05 and pulse width 10µs. The pulse current is limited by the maximum junction temperature.
- 9. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s;$  duty cycle  $\leq 2\%.$
- 10. For design aid only, not subject to production testing.
- 11. Switching characteristics are independent of operating junction temperatures.

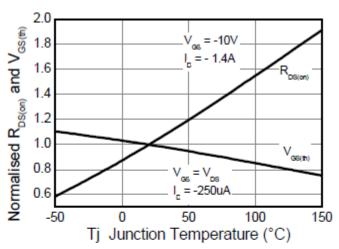




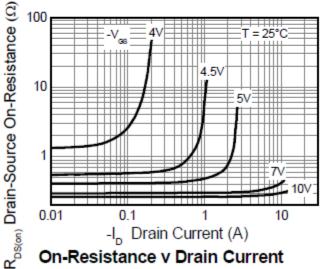




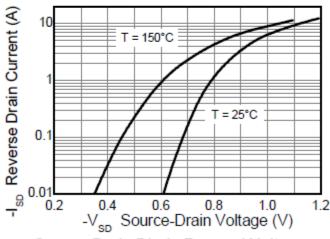
**Typical Transfer Characteristics** 



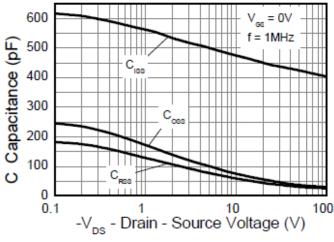
Normalised Curves v Temperature



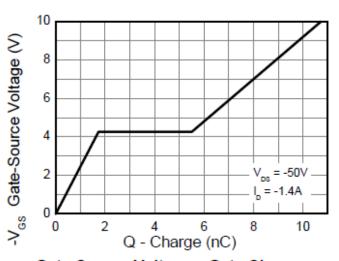
On-Resistance v Drain Current



Source-Drain Diode Forward Voltage



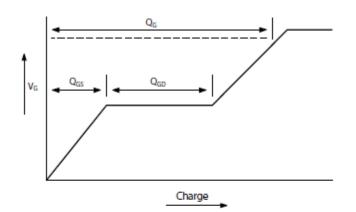
Capacitance v Drain-Source Voltage



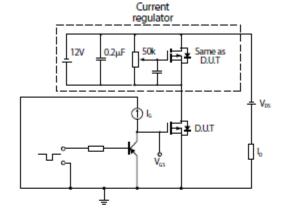
Gate-Source Voltage v Gate Charge



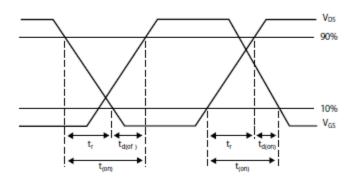
## **Test Circuits**



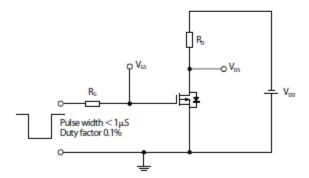
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

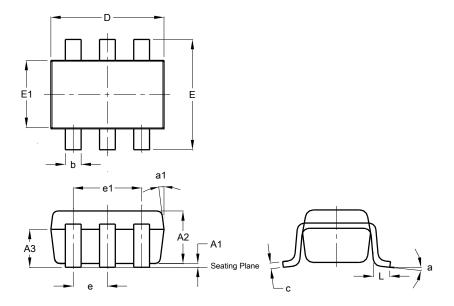


Switching time test circuit



# **Package Outline Dimensions**

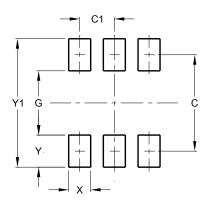
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26							
Dim	Min	Max	Тур					
A1	0.013	0.10	0.05					
A2	1.00	1.30	1.10					
А3	0.70	0.80	0.75					
b	0.35	0.50	0.38					
С	0.10	0.20	0.15					
D	2.90	3.10	3.00					
е	-	-	0.95					
e1	-	-	1.90					
Е	2.70	3.00	2.80					
E1	1.50	1.70	1.60					
L	0.35	0.55	0.40					
а	-	-	8°					
a1	-	-	7°					
All	Dimen	All Dimensions in mm						

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Υ	0.80
Y1	3.20



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